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## STPS1L20M

### LOW DROP POWER SCHOTTKY RECTIFIER

**Table 1: Main Product Characteristics** 

| I <sub>F(AV)</sub>   | 1 A    |
|----------------------|--------|
| V <sub>RRM</sub>     | 20 V   |
| T <sub>j</sub> (max) | 150°C  |
| V <sub>F</sub> (max) | 0.37 V |

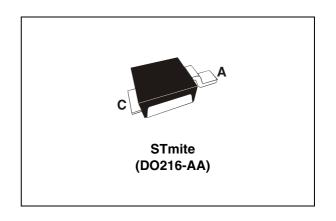
### **FEATURES AND BENEFITS**

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop for higher efficiency and extented battery life
- Low thermal resistance
- Avalanche capability specified

### **DESCRIPTION**

Single Schottky rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in STmite, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications. Due to the small size of the package this device fits battery powered equipment (cellular, notebook, PDA's, printers) as well chargers and PCMCIA cards.



**Table 2: Order Code** 

| Part Number | Marking |
|-------------|---------|
| STPS1L20M   | 1L2     |

Table 3: Absolute Ratings (limiting values)

| Symbol              | Parameter   | Value               | Unit |   |
|---------------------|---|---------------------|------|---|
| $V_{RRM}$           | Repetitive peak reverse voltage                                       |                     | 20   | V |
| I <sub>F(RMS)</sub> | RMS forward voltage   | RMS forward voltage |      |   |
| I <sub>F(AV)</sub>  | Average forward current $T_c = 140^{\circ}C$ $\delta = 0.5$           |                     | 1    | Α |
| I <sub>FSM</sub>    | Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$ |                     | 50   | Α |
| P <sub>ARM</sub>    | Repetitive peak avalanche power $t^p = 1 \mu s$ $T^j = 25$ °C         |                     | 1400 | W |
| T <sub>stg</sub>    | Storage temperature range   | -65 to + 150        | °C   |   |
| T <sub>j</sub>      | Maximum operating junction temperature                                | 150                 | °C   |   |
| dV/dt               | Critical rate of rise of reverse voltage (ra                          | 10000               | V/µs |   |

<sup>\*:</sup>  $\frac{dPtot}{dTj} > \frac{1}{Rth(j-a)}$  thermal runaway condition for a diode on its own heatsink

**Table 4: Thermal Resistance** 

| Symbol                 | Parameter           | Value | Unit |
|------------------------|---------------------|-------|------|
| R <sub>th(j-c)</sub>   | Junction to case    | 20    | °C/W |
| R <sub>th(j-l)</sub> * | Junction to ambient | 250   | °C/W |

<sup>\*</sup> Mounted with minimum recommended pad size, PC board FR4.

**Table 5: Static Electrical Characteristics** 

| Symbol                                   | Parameter             | Tests conditions                           |                     | Min.  | Тур   | Max.  | Unit |
|--|-----------------------|--|---------------------|-------|-------|-------|------|
| I <sub>R</sub> * Reverse leakage current |                       | T <sub>j</sub> = 25°C                      | $V_R = V_{RRM}$     |       | 0.015 | 0.075 |      |
|  | T <sub>j</sub> = 85°C | VR − VRRM                                  |                     | 0.9   | 4.5   |       |      |
|  | T <sub>j</sub> = 25°C | V <sub>R</sub> = 10V                       |                     | 0.005 | 0.035 | mΛ    |      |
|  | T <sub>j</sub> = 85°C |  |                     | 0.45  | 2.5   | mA    |      |
|  | T <sub>j</sub> = 25°C | $V_R = 5V$                                 |                     | 0.003 | 0.025 |       |      |
|  |                       | T <sub>j</sub> = 85°C                      |                     |       | 0.3   | 1.6   |      |
|  |                       | T <sub>j</sub> = 25°C                      | I <sub>F</sub> = 1A |       | 0.38  | 0.43  |      |
| V <sub>F</sub> * Forward voltage dro     | Forward valtage drap  | T <sub>j</sub> = 85°C                      | IF - IA             |       | 0.32  | 0.37  | V    |
|  | Forward voltage drop  | $T_j = 25^{\circ}C$<br>$T_j = 85^{\circ}C$ | I <sub>F</sub> = 3A |       | 0.46  | 0.53  | V    |
|  |                       | T <sub>j</sub> = 85°C                      | 1F - 0A             |       | 0.42  | 0.49  |      |

To evaluate the conduction losses use the following equation:  $P = 0.31 \times I_{F(AV)} + 0.06 I_{F(RMS)}^2$ 

Figure 1: Conduction losses versus average current

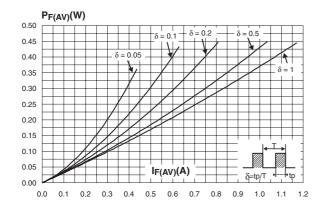


Figure 2: Average forward current versus ambient temperature ( $\delta$  = 0.5)

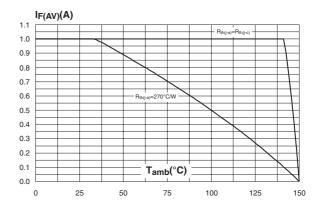


Figure 3: Normalized avalanche power derating versus pulse duration

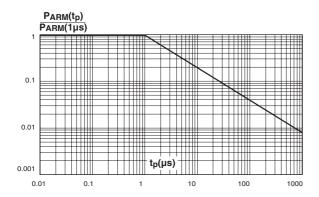


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values)

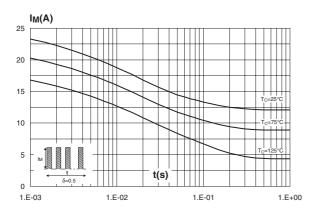


Figure 7: Reverse leakage current versus reverse voltage applied (typical values)

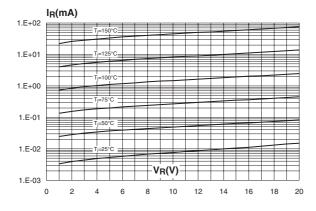


Figure 4: Normalized avalanche power derating versus junction temperature

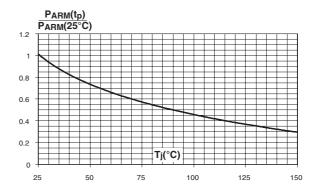


Figure 6: Relative variation of thermal impedance junction to ambient versus pulse duration

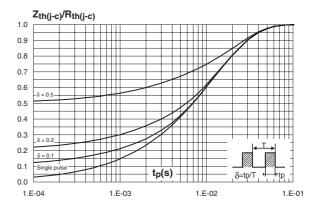
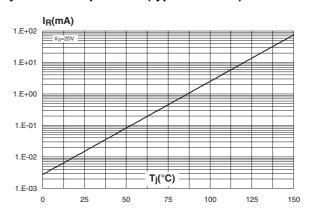


Figure 8: Reverse leakage current versus junction temperature (typical values)



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Figure 9: Junction capacitance versus reverse voltage applied (typical values)

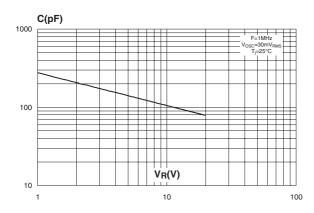


Figure 11: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4,  $Cu = 35\mu m$ , typical values)

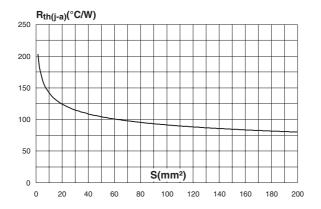
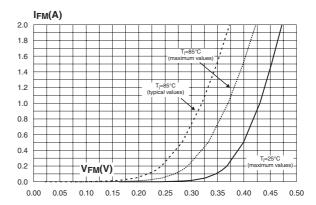
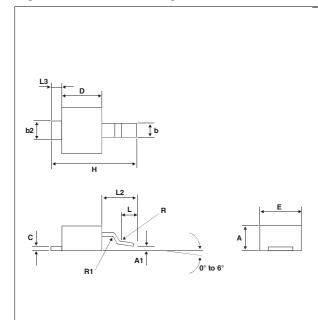


Figure 10: Forward voltage drop versus forward current



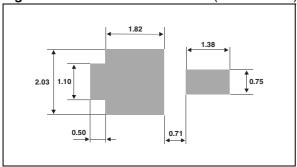
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Figure 12: STmite Package Mechanical Data



|      | DIMENSIONS |      |      |        |       |       |
|------|------------|------|------|--------|-------|-------|
| REF. | Millime    |      | rs   |        |       |       |
|      | Min.       | Тур. | Max. | Min.   | Тур.  | Max.  |
| Α    | 0.85       | 1.00 | 1.15 | 0.033  | 0.039 | 0.045 |
| A1   | -0.05      |      | 0.05 | -0.002 |       | 0.002 |
| b    | 0.40       |      | 0.65 | 0.016  |       | 0.025 |
| b2   | 0.70       |      | 1.00 | 0.027  |       | 0.039 |
| С    | 0.10       |      | 0.25 | 0.004  |       | 0.010 |
| D    | 1.75       | 1.90 | 2.05 | 0.069  | 0.007 | 0.081 |
| Е    | 1.75       | 1.90 | 2.05 | 0.069  | 0.007 | 0.081 |
| Н    | 3.60       | 3.75 | 3.90 | 0.142  | 0.148 | 0.154 |
| L    | 0.50       | 0.63 | 0.80 | 0.020  | 0.025 | 0.031 |
| L2   | 1.20       | 1.35 | 1.50 | 0.047  | 0.053 | 0.059 |
| L3   |            | 0.50 |      |        | 0.019 |       |
|      |            | ref  |      |        | ref   |       |
| R    | 0.07       |      |      | 0.003  |       |       |
| R1   | 0.07       |      |      | 0.003  |       |       |

Figure 13: Foot Print Dimensions (in millimeters)



**Table 6: Ordering Information** 

| Ordering type | Marking | Package | Weight  | Base qty | Delivery mode |
|---------------|---------|---------|---------|----------|---------------|
| STPS1L20M     | 1L2     | STmite  | 15.5 mg | 12000    | Tape & reel   |

**Table 7: Revision History** 

| Date        | Revision | Description of Changes   |
|-------------|----------|--|
| Jul-2003    | 2A       | Last update.   |
| 13-Sep-2004 | 3        | STmite package dimensions reference A1 change: from blank (min) to -0.05mm and from 0.10 (max) to 0.05mm.  |
| 29-Nov-2005 | 4        | Page 2, table 5: conduction losses evaluation values changed:  From P = $0.34 \times I_{F(AV)} + 0.07 I_{F}^{2}_{(RMS)}$ To P = $0.31 \times I_{F(AV)} + 0.06 I_{F}^{2}_{(RMS)}$ |

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